



SOT-23 Plastic-Encapsulate Diodes

BAS19LT1 SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^{\circ}C$)

Forward Current

I_F : 200 mA

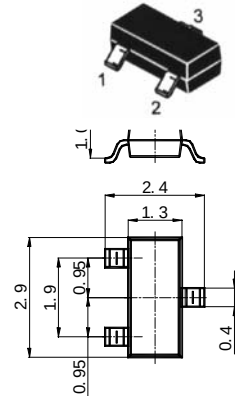
Reverse Voltage

V_R : 120 V

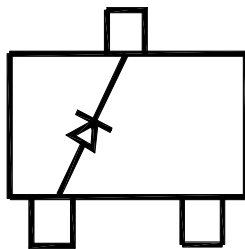
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23



Unit: mm



Marking JP

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	120		V
Reverse voltage leakage current	I_R	$V_R=100V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}			50	nS